

Inventor: Kennedy et al.  
Serial No.: 09/547,167  
Atty Dkt. No. 100595.0052US1

Art Unit: 2822  
Examiner: C. Novacek



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
WASHINGTON, D.C. 20231**

Inventor: **Kennedy et al.**  
Serial No: **09/547,167**  
Filed: **April 11, 2000**  
For: **The Use of Sacrificial  
Inorganic Dielectrics for  
Dual Damascene Processes  
Utilizing Organic Intermetal  
Dielectrics**

Examiner: C. Novacek  
Art Unit: 2822

Attorney Docket No.: 595.052-US1

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**PRELIMINARY AMENDMENT**

**IN THE CLAIMS**

Please find below a Clean Copy of Claims for Examiner's Immediate Reference. A Marked Up Copy and Additional Clean Copy are herein attached.

1. (Twice Amended) A method of making conducting vias and conducting lines on a substrate comprising:  
  
depositing a stack having a top surface on a substrate, wherein the stack comprises a first organic intermetal dielectric layer and a hardmask layer, wherein the hardmask layer comprises a material comprising silicon oxynitride or silicon oxide;  
  
forming a via opening in said stack;  
  
depositing a sacrificial inorganic dielectric in the via opening, wherein the sacrificial inorganic dielectric substantially filling the via opening and substantially covering the top surface of the stack;